P-Ch 150V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

Green

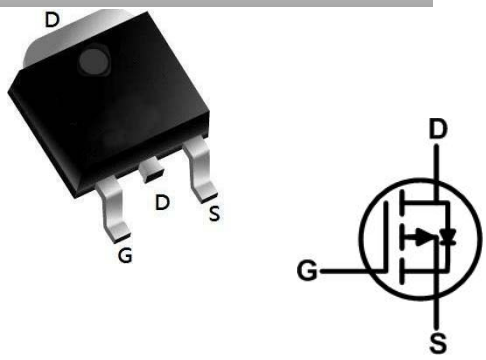
BVDSS	RDSON	ID
-150V	77mΩ	-30A

Description

The XR30P15 is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XR30P15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	-30	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	-16	A
I_{DM}	Pulsed Drain Current[2]	-100	A
EAS	Single Pulse Avalanche Energy[3]	380	mJ
I_{AS}	Avalanche Current	---	A
P_D@T_C=25℃	Total Power Dissipation[4]	23	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	---	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	2.1	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-150	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-12A	---	77	104	mΩ
		V_{GS}=-4.5V , I_D=-8A	---	78	105	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1	-1.8	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-150V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-150V, V_{GS}=0V , T_J=100℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-3	---	11	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.8	---	Ω
Q_g	Total Gate Charge	V_{DS}=-75V , V_{GS}=-10V , I_D=-3A	---	142	---	nC
Q_{gs}	Gate-Source Charge		---	26.7	---	
Q_{gd}	Gate-Drain Charge		---	50	---	
$T_{d(on)}$	Turn-On Delay Time	V_{GS}=-10V, V_{DS}=-75V, ID= -3A, R_{GEN}=3Ω	---	36.2	---	ns
T_r	Rise Time		---	136	---	
$T_{d(off)}$	Turn-Off Delay Time		---	85	---	
T_f	Fall Time		---	60	---	
C_{iss}	Input Capacitance	V_{DS}=-75V , V_{GS}=0V , f=1MHz	---	8178	---	pF
C_{oss}	Output Capacitance		---	127	---	
C_{rss}	Reverse Transfer Capacitance		---	114	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-3A , T_J=25℃	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	IF=-3A ,di/dt=100A / μs , T_J= 2 5 ℃	---	88	---	nS
Q_{rr}	Reverse Recovery Charge		---	182	---	nC

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C
2. The EAS data shows Max. rating . The test condition is DD=-50V, VG=-10V, RG=25ohm, L=0.5mH
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

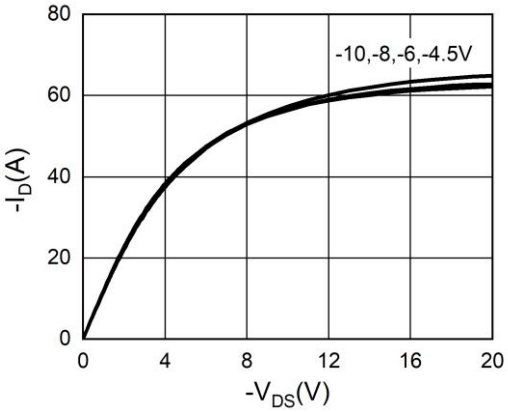


Figure 2. Transfer Characteristics

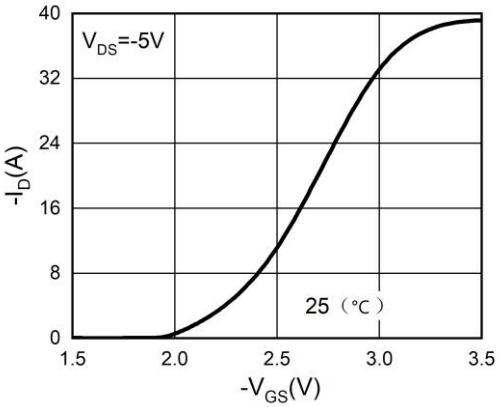


Figure 3. Power Dissipation

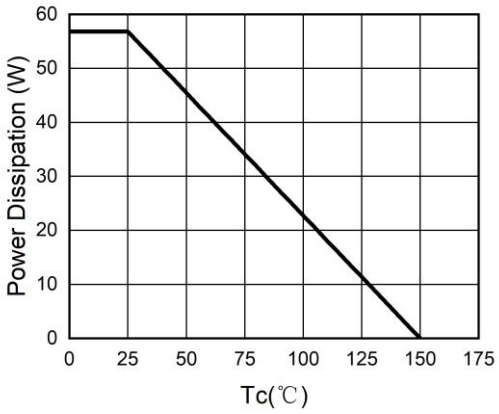


Figure 4. Drain Current

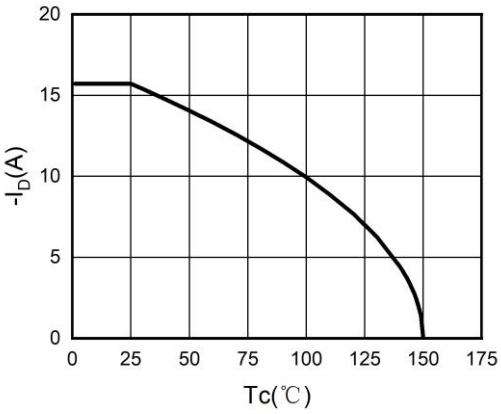


Figure 5. BV_{DSS} vs Junction Temperature

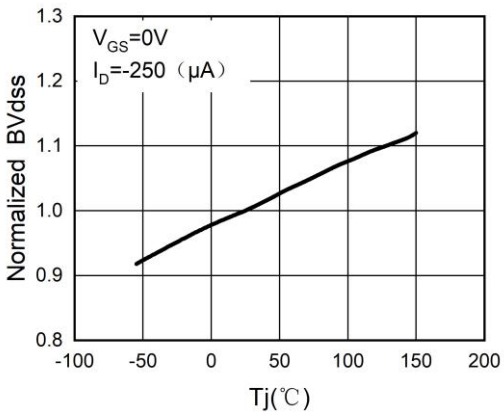
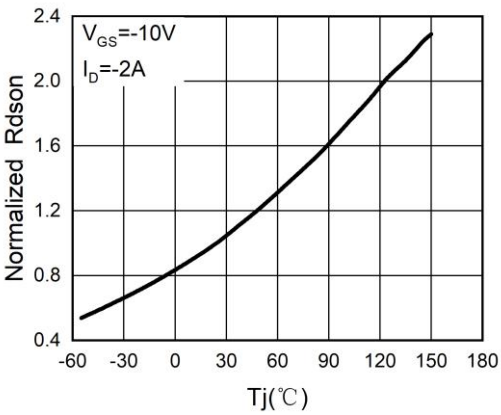


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

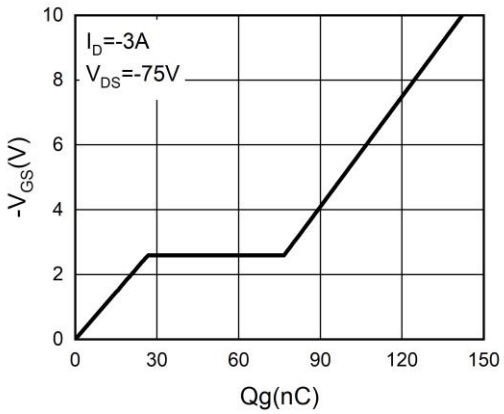


Figure 8. Capacitance

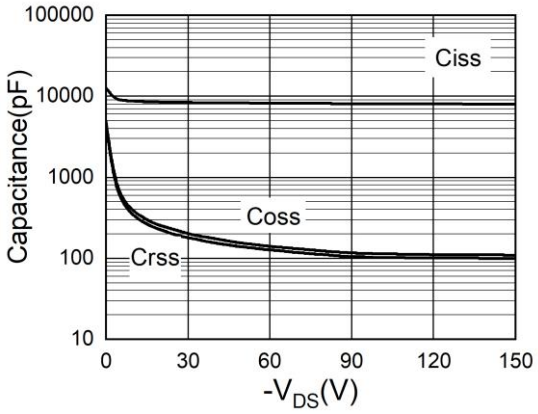


Figure 9. Body-Diode Characteristics

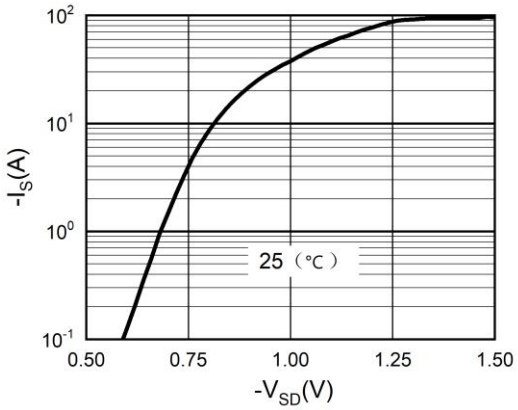
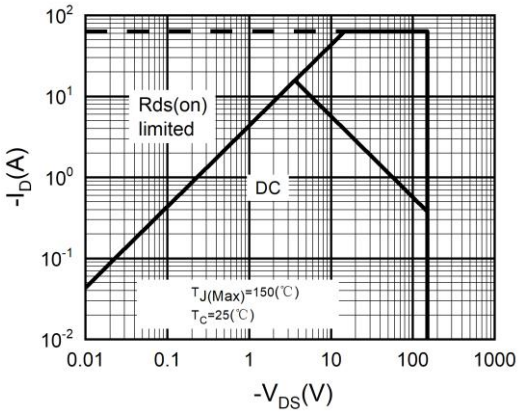
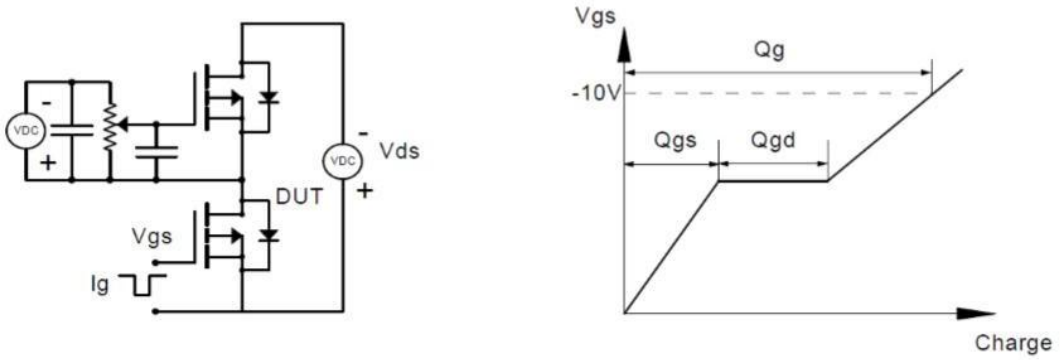


Figure 10. Maximum Safe Operating Area

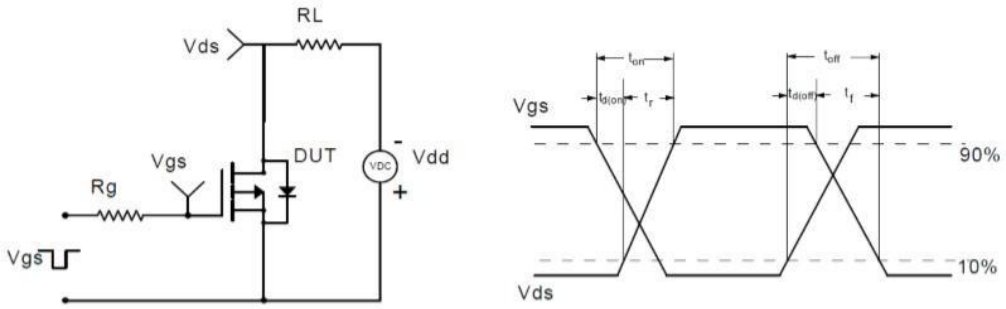


Test Circuit

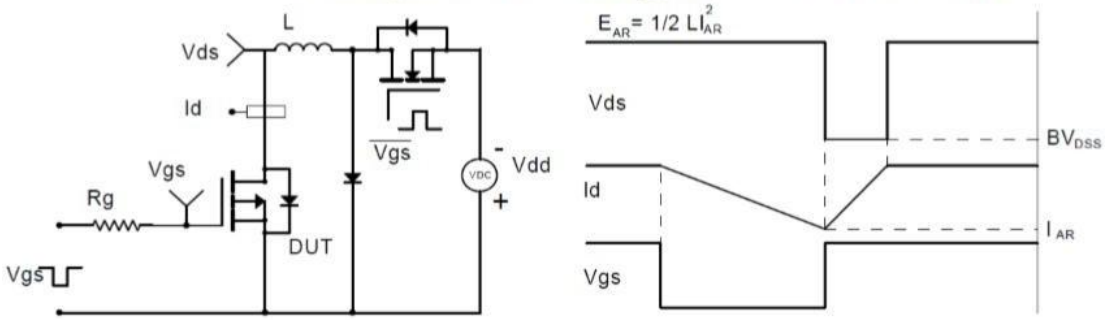
Gate Charge Test Circuit & Waveform



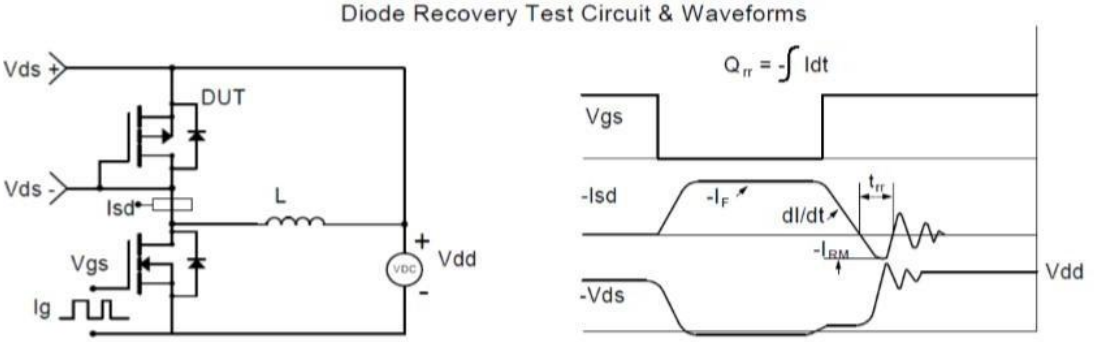
Resistive Switching Test Circuit & Waveforms



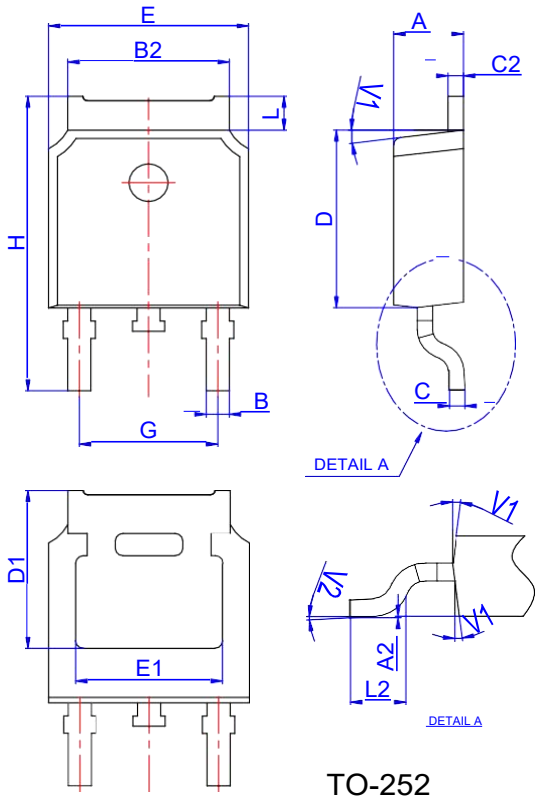
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



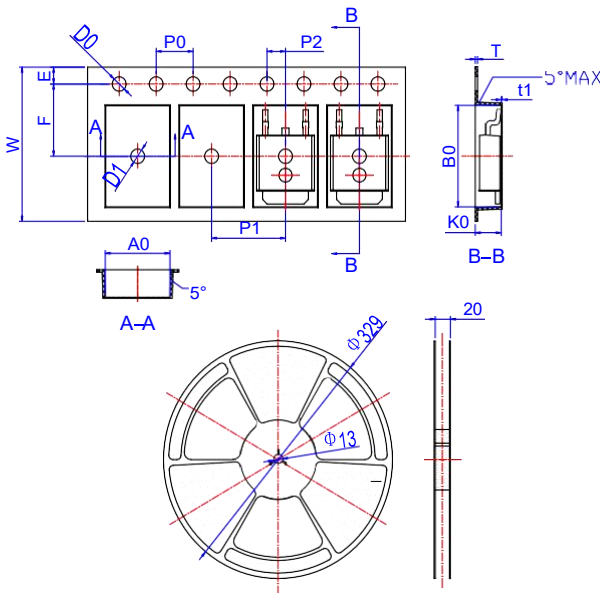
Package Mechanical Data-TO-252



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Spectification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583